

**Key Parameters**

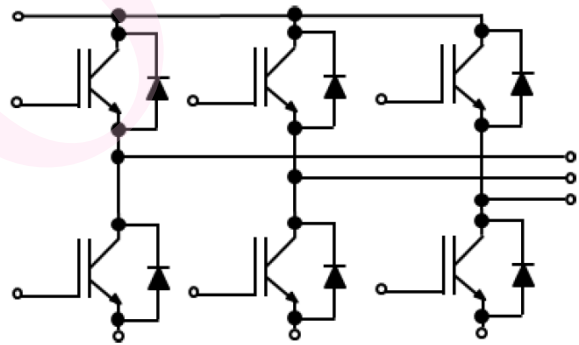
V_{CES}	= 650V
I_c	= 20A

Features

- Low $V_{ce(sat)}$
- Fast switching
- High ruggedness
- High short circuit capability

Applications

- Inverter for motor drive
- Water pumps
- Wind turbines



Equivalent Circuit Schematic

Prepared by : ABA

Date of Publication : 10.2022

Approved by :

Revision : 1

Absolute Maximum Ratings: IGBT, Inverter						
Symbol	Characteristic	Value	Unit			
V_{CES}	Collector-Emitter Voltage	650	V			
I_{CDC}	Continuous DC Collector Current ($T_c=85^\circ\text{C}$)	20	A			
I_{CRM}	Peak Collector Current	40	A			
V_{GES}	Gate-Emitter Voltage	± 20	V			
$P_{D(max)}$	Total Power Dissipation ($T_c=25^\circ\text{C}$, $T_j=175^\circ\text{C}$)	70	W			
IGBT Characteristics						
Symbol	Characteristic	Conditions	Value			Unit
			Min.	Typ.	Max.	
BV_{CES}	Collector-Emitter breakdown Voltage	$V_{GE}=0V, I_C=250\mu\text{A}, T_{vj}=25^\circ\text{C}$	650			V
I_{CES}	Collector-Emitter leakage Current	$V_{CE}=650V, V_{GE}=0V, T_{vj}=25^\circ\text{C}$			1.0	mA
I_{GES}	Gate-Emitter leakage Current	$V_{CE}=0V, V_{GE}=\pm 20V, T_{vj}=25^\circ\text{C}$			400	ηA
$V_{GE(th)}$	Gate-emitter Threshold Voltage	$V_{GE}=V_{CE}, I_C=250\mu\text{A}, T_{vj}=25^\circ\text{C}$	5.0	6.0	7.0	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=20A, V_{GE}=15V, T_{vj}=25^\circ\text{C}$		1.70	2.00	V
		$I_C=20A, V_{GE}=15V, T_{vj}=150^\circ\text{C}$		2.15		V
Q_G	Gate Charge	$V_{CC}=300V, V_{GE}=0/15V, I_C=20A, T_{vj}=25^\circ\text{C}$		45		ηC
C_{iss}	Input Capacitance	$V_{CE}=25V, V_{GE}=0V, f=1\text{MHz}, T_{vj}=25^\circ\text{C}$		0.93		ηF
C_{oss}	Output Capacitance			0.085		ηF
C_{rss}	Reverse Transfer Capacitance			0.016		ηF
$t_{d(on)}$	Turn-on Delay Time	$I_C=20\text{ A}$ $V_{CE}=300\text{ V}$ $V_{GE}=\pm 15\text{ V}$ $R_G=22\Omega$ $T_{vj}=25^\circ\text{C}, L_{load}=0.82\text{mH}$ Energy loss include tail and diode reverse recovery		29		ηs
t_r	Rise Time			44		ηs
$t_{d(off)}$	Turn-off Delay Time			77		ηs
t_f	Fall Time			94		ηs
E_{on}	Energy Dissipation During Turn-on Time			0.4		mJ
E_{off}	Energy Dissipation During Turn-off Time			0.28		mJ
$t_{d(on)}$	Turn-on Delay Time	$I_C=20A$ $V_{CE}=300\text{ V}$ $V_{GE}=\pm 15\text{ V}$ $R_G=22\Omega$ $T_{vj}=150^\circ\text{C}, L_{load}=0.82\text{mH}$ Energy loss include tail and diode reverse recovery		30		ηs
t_r	Rise Time			46		ηs
$t_{d(off)}$	Turn-off Delay Time			97		ηs
t_f	Fall Time			135		ηs
E_{on}	Energy Dissipation During Turn-on Time			0.6		mJ
E_{off}	Energy Dissipation During Turn-off Time			0.38		mJ
$I_{C(SC)}$	SC Data	$t_{sc}\leq 5\mu\text{s}, V_{GE}=15V, T_{vj}=25^\circ\text{C}, V_{CC}\leq 400V,$		60		A
			Prepared by : ABA	Date of Publication : 10.2022		
			Approved by :	Revision : 1		

Absolute Maximum Ratings: Diode, Inverter						
Symbol	Characteristic		Value			Unit
V _{RRM}	Repetitive peak reverse voltage		650			V
I _F	Continuous DC forward current (T _c =85°C)		20			A
I _{FRM}	Repetitive peak forward current		40			A
Diode Characteristics						
Symbol	Characteristic	Conditions	Value			Unit
			Min.	Typ.	Max.	
V _F	Forward Voltage	I _F =20A, T _{vj} =25°C		1.4	1.7	V
		I _F =20A, T _{vj} =150°C		1.2		V
Q _{rr}	Recovered Charge	I _F = 20 A		0.33		μC
I _{rrm}	Peak Reverse Recovery Current	V _R =300V		8.4		A
E _{rr}	Reverse Recovery Energy	-di _F /dt = 367A/μs T _{vj} =25°C		0.02		mJ
Module Characteristics						
Symbol	Characteristic	Conditions	Value			Unit
			Min.	Typ.	Max.	
V _{isol}	Isolation voltage	t=1min, f=50Hz	2500			V
T _{jmax}	Maximum Junction Temperature				175	°C
T _{vj op}	Operating Junction Temperature		-40		150	°C
T _{stg}	Storage Temperature		-40		125	°C
R _{CC'+EE'}	Module lead resistance terminal to chip			9.5		mΩ
L _{SCE}	Stray Inductance, Module			25		nH
R _{θjc}	Junction-to Case	per IGBT-inverter		1.95		°C/W
		per Diode-inverter		2.5		°C/W
R _{θcs}	Case to Sink	per IGBT-inverter		0.81		°C/W
		per Diode-inverter		1.0		°C/W
M _t	Module force for module mounting		30		50	N
G	Weight of Module			10		g
			Prepared by : ABA		Date of Publication : 10.2022	
			Approved by :		Revision : 1	

• Typical Electrical Characteristics

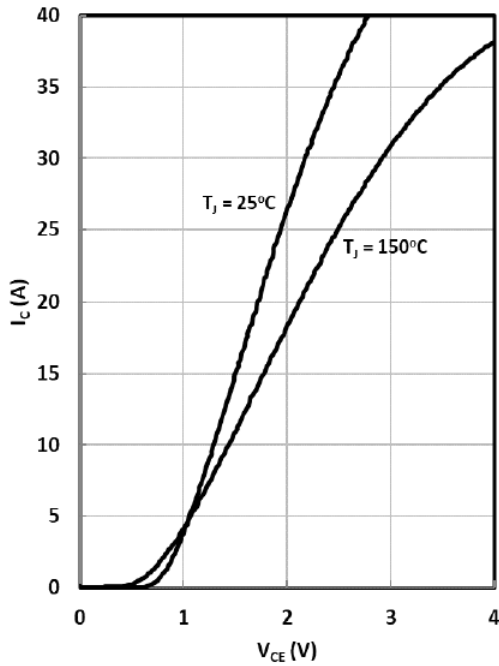


Fig. 1 IGBT (Inverter) Output Characteristics

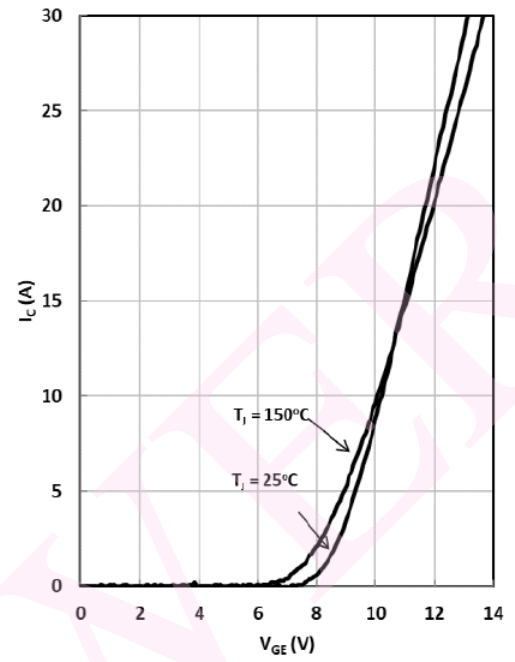


Fig. 2 IGBT (Inverter) Transfer Characteristics

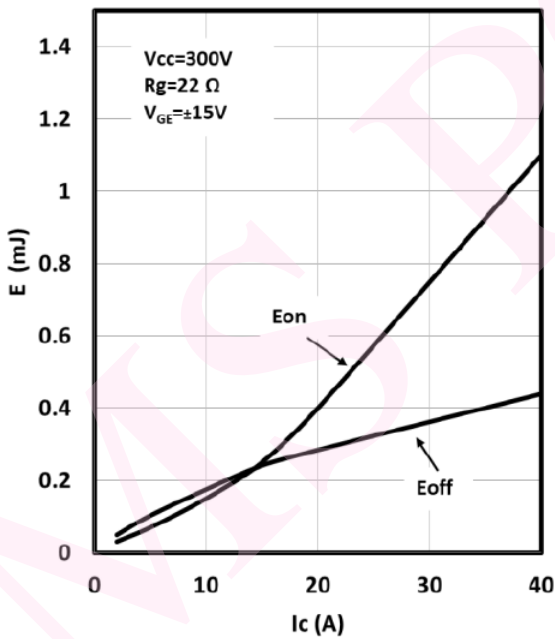


Fig. 3 IGBT (Inverter) Switching Loss vs. Ic

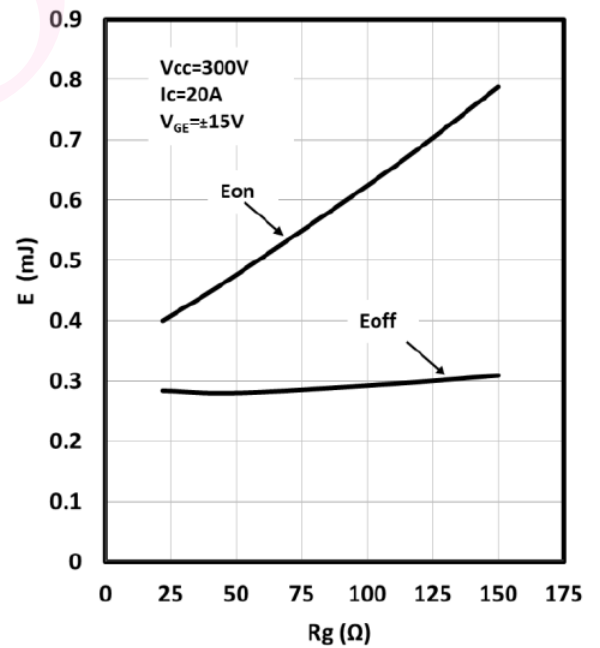


Fig. 4 IGBT (Inverter) Switching Loss vs. Rg

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Approved by :	Revision : 1

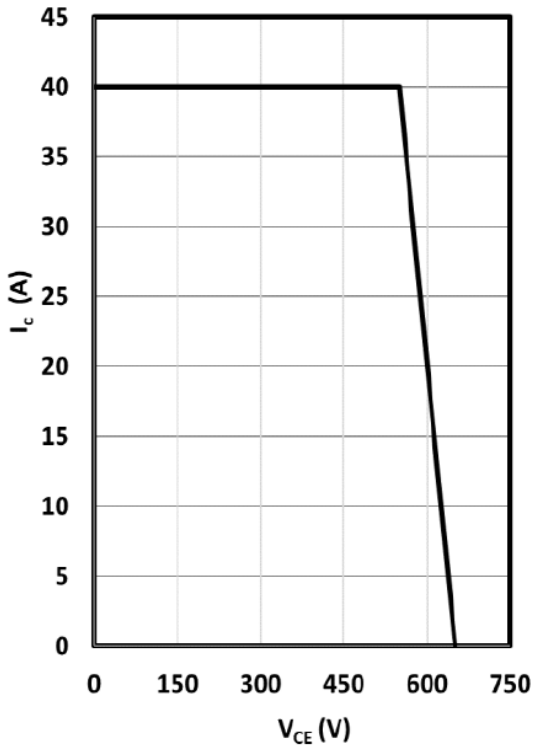


Fig. 5 RBSOA

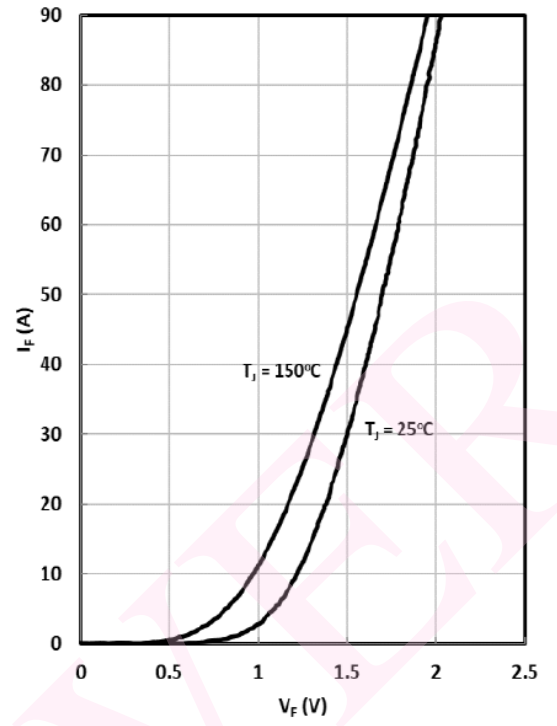
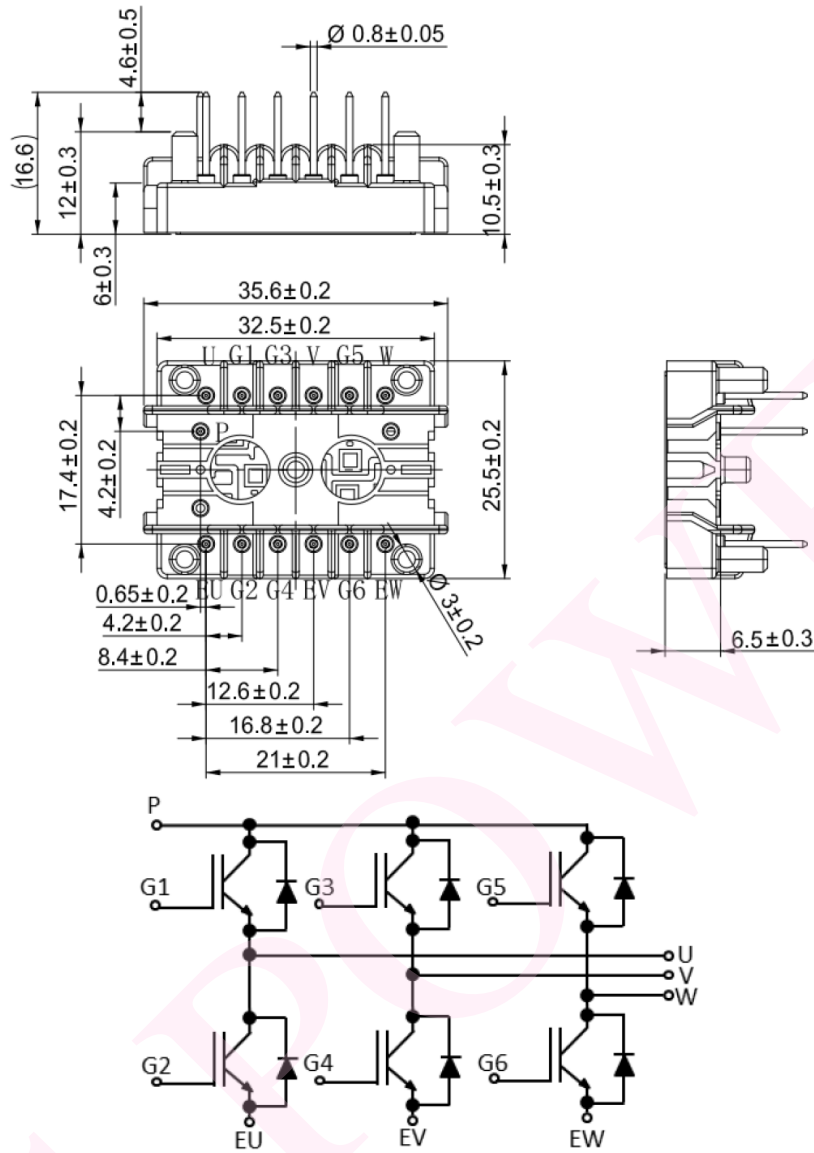


Fig. 6 Diode (Inverter) Forward Characteristics

Prepared by : ABA	Date of Publication : 10.2022
Approved by :	Revision : 1

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Prepared by : ABA	Date of Publication : 10.2022
Approved by :	Revision : 1